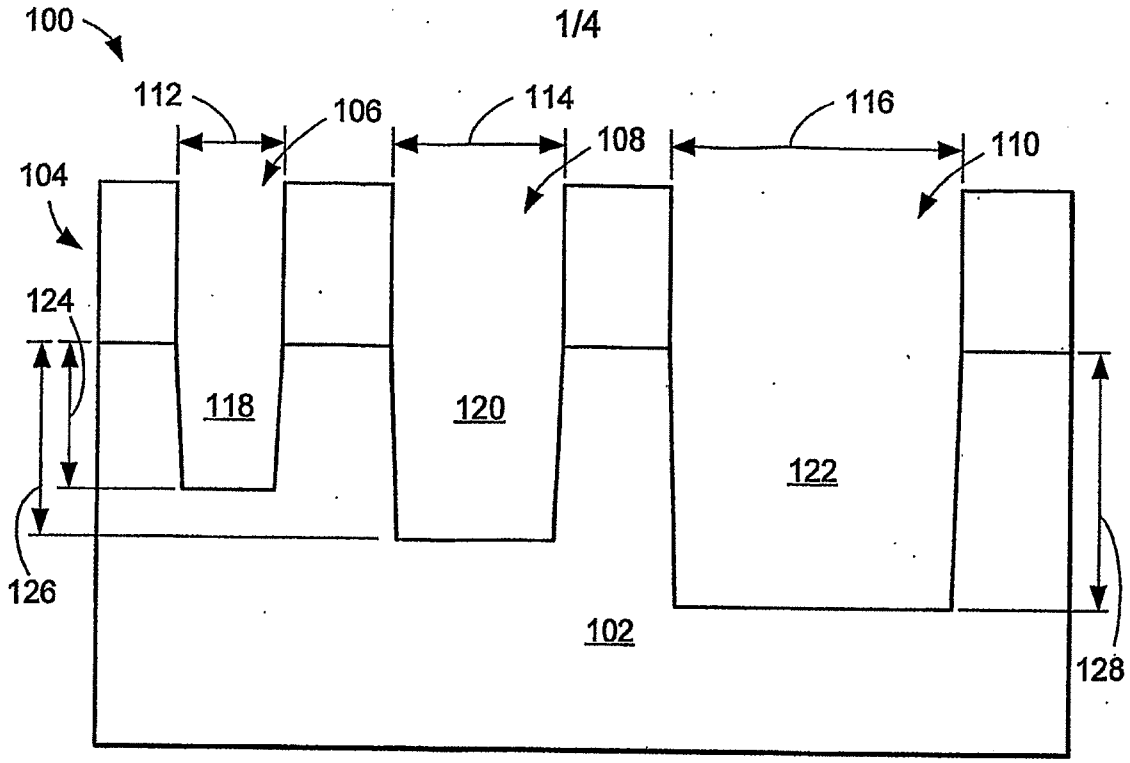

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FIG. 1

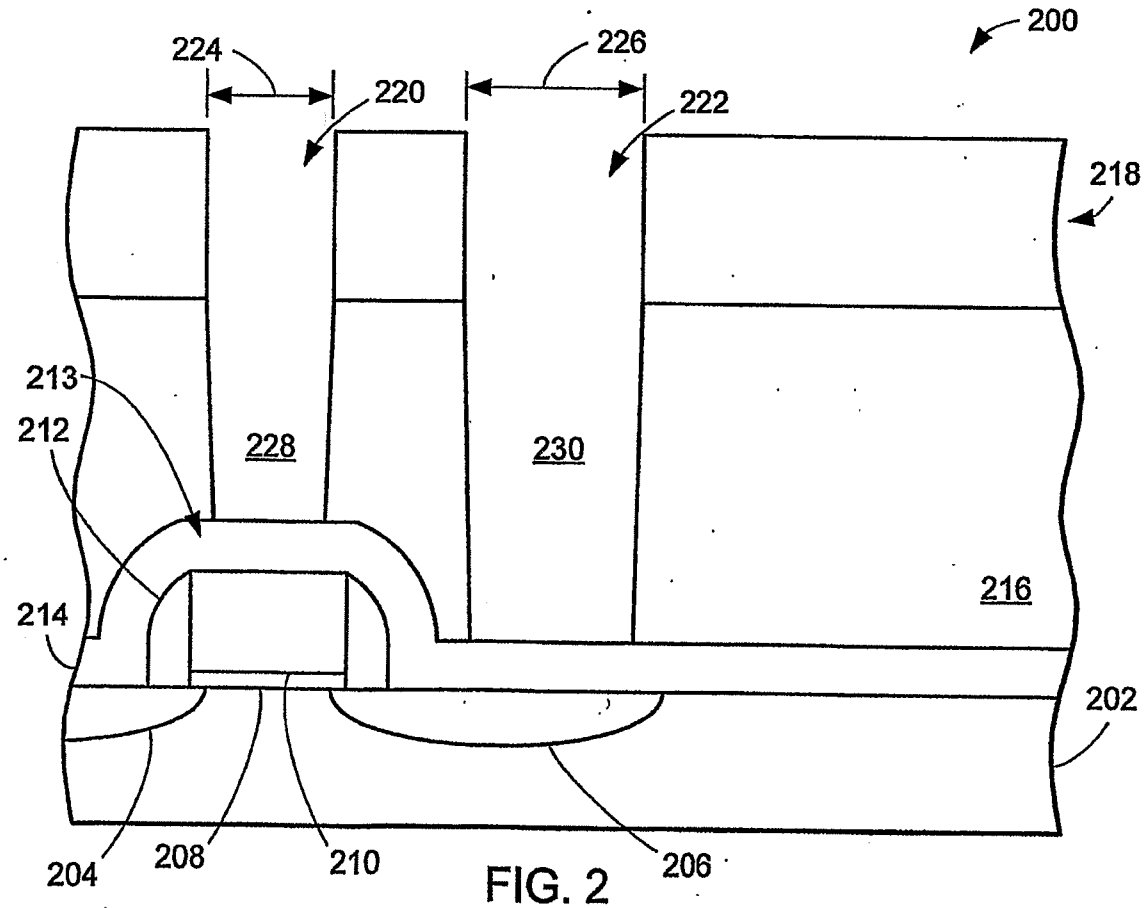

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FIG. 2

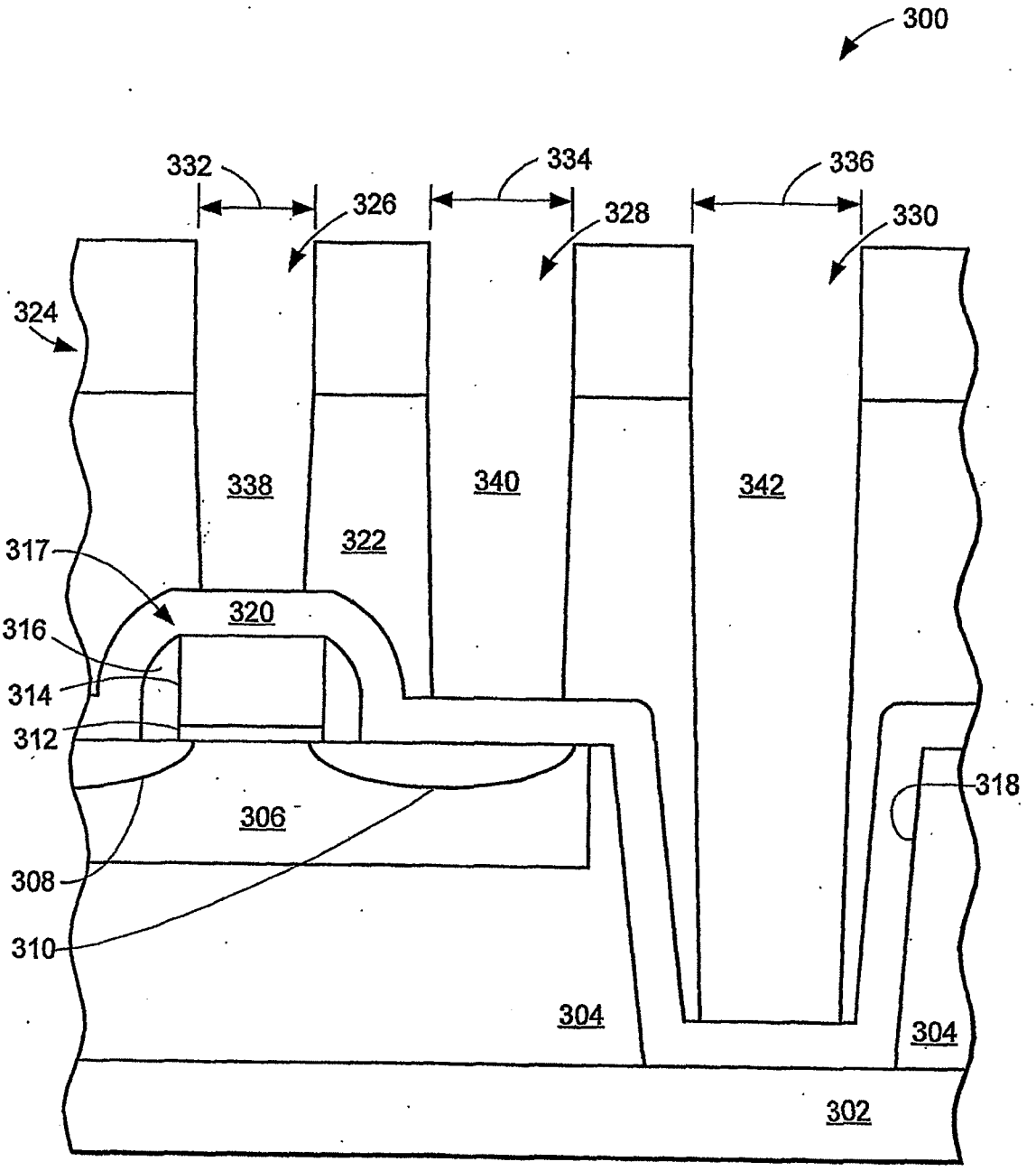

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FIG. 3

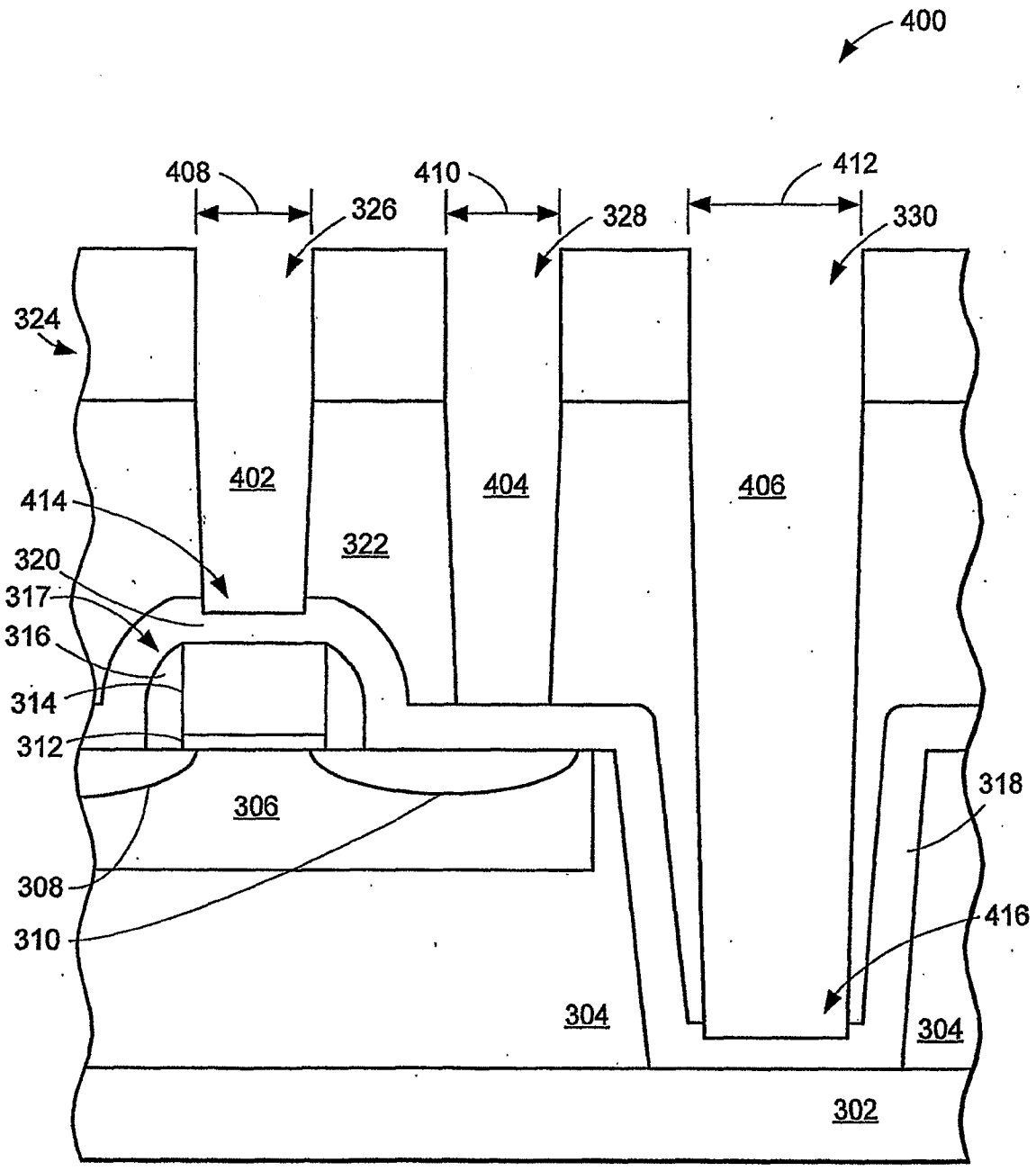

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FIG. 4

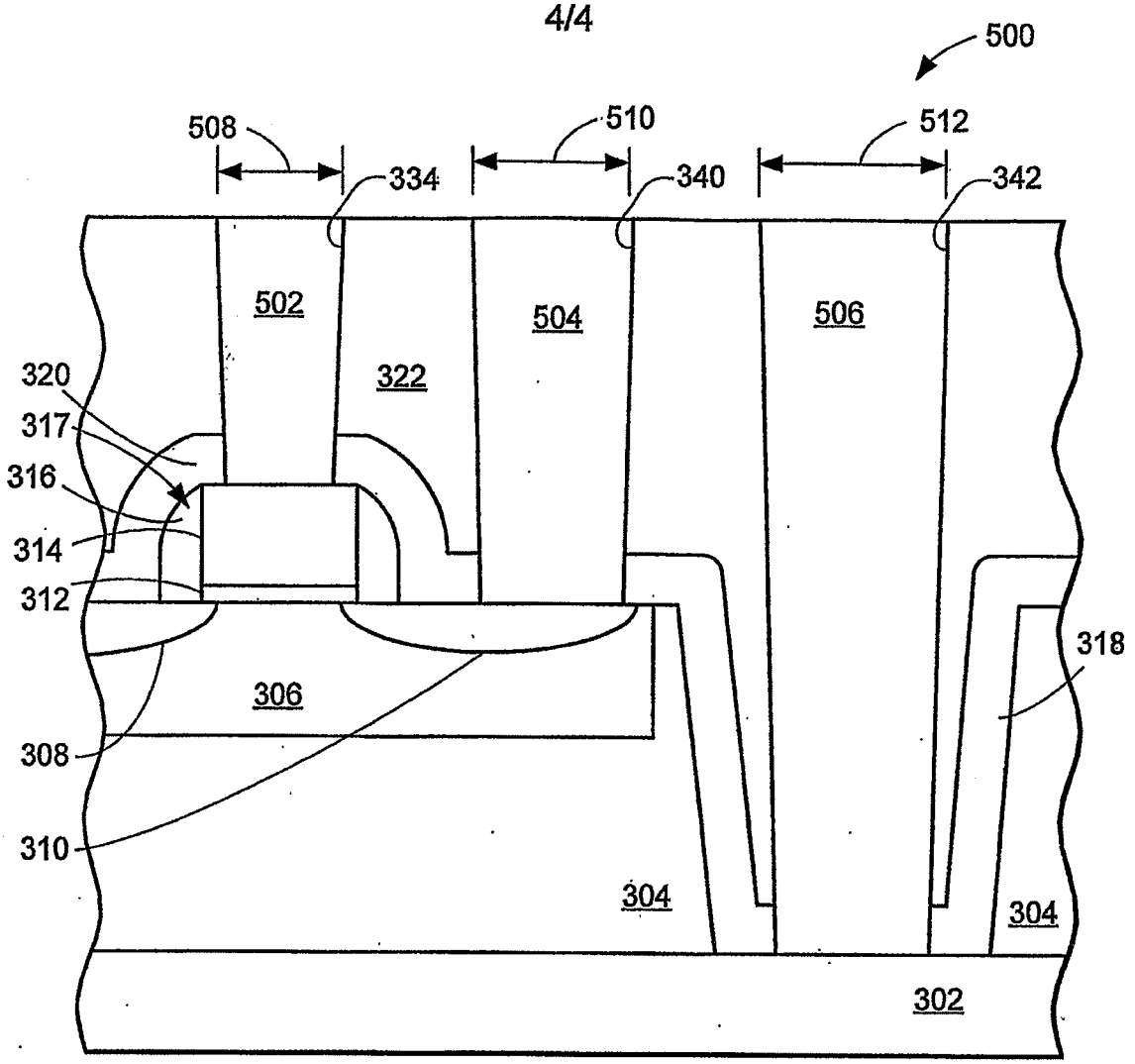

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FIG. 5

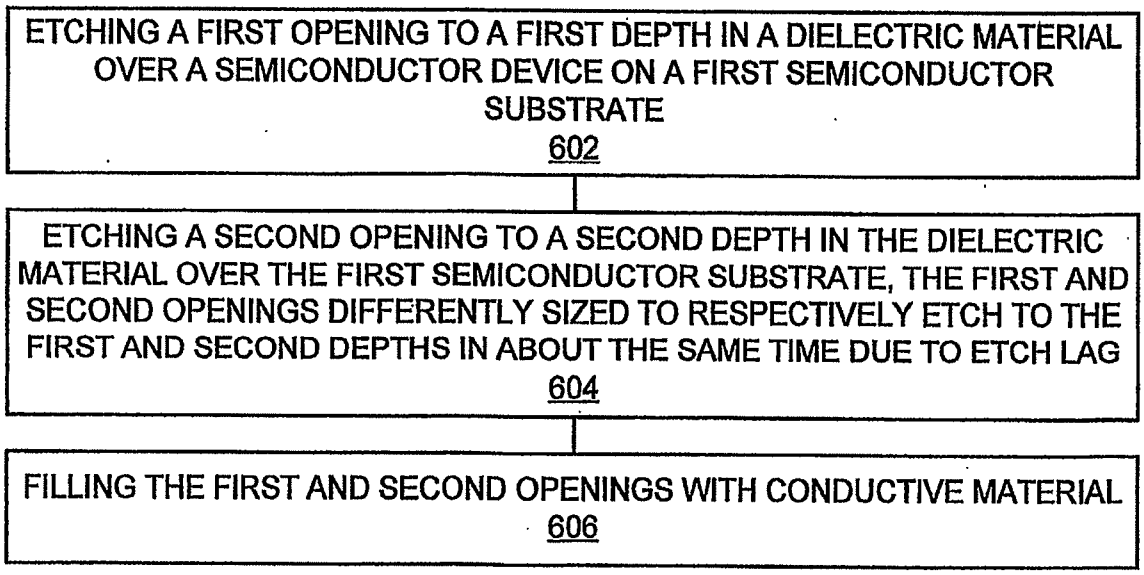

ETCHING A FIRST OPENING TO A FIRST DEPTH IN A DIELECTRIC MATERIAL OVER A SEMICONDUCTOR DEVICE ON A FIRST SEMICONDUCTOR SUBSTRATE
602
ETCHING A SECOND OPENING TO A SECOND DEPTH IN THE DIELECTRIC MATERIAL OVER THE FIRST SEMICONDUCTOR SUBSTRATE, THE FIRST AND SECOND OPENINGS DIFFERENTLY SIZED TO RESPECTIVELY ETCH TO THE FIRST AND SECOND DEPTHS IN ABOUT THE SAME TIME DUE TO ETCH LAG
604
FILLING THE FIRST AND SECOND OPENINGS WITH CONDUCTIVE MATERIAL
606
600

FIG. 6